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LINDA E. HASTINGS

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Attorney Docket No.: NECW 18.281

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED
OCT -2 2002
TECHNOLOGY CENTER 2809

Inventor: Toru TATSUMI et al.

Serial No.: 09/744,701

Filed: January 29, 2001

Title: **METHOD OF VAPOR PHASE GROWTH OF METAL OXIDE
DIELECTRIC FILM AND APPARATUS FOR VAPOR PHASE
GROWTH OF METAL DIELECTRIC MATERIAL**

Examiner: H. Jey Tsai

Group Art Unit: 2812

Assistant Commissioner for Patents
Washington, D.C. 20231

ELECTION

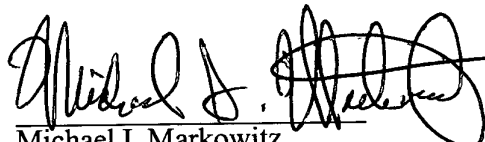
S I R :

In response to the Office Action mailed on August 27, 2002, the period for responding thereto having been set to expire after September 27, 2002, Applicant hereby elects the first species of a vapor phase growth method for forming metal oxide dielectric film, for prosecution at this time.

Claims 47-90 are readable on the first species. Claims 47-90 are clearly directed to the vapor phase growth method for forming metal oxide dielectric film. Claims 91-94 are also related to the elected species because the method of claims 91-94 uses the vapor phase growth method of the elected species as one of the steps of forming a semiconductor device. Applicant reserves the right to file continuing application(s) based on the second species of forming a capacitor, if the Examiner makes the Election Requirement to which this Election is responsive, final. Early examination on the merits is earnestly solicited.

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Respectfully submitted,



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